

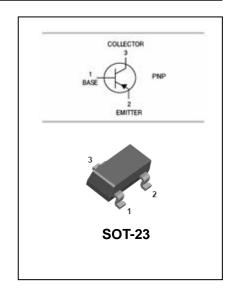
# Diode Semiconductor Korea

# Silicon Epitaxial Planar Transistor

**S8550** 

## **FEATURES**

- High Collector Current.(I<sub>C</sub>= -500mA)
- Complementary To S8050.
- Excellent H<sub>FE</sub> Linearity.



#### **APPLICATIONS**

High Collector Current.

#### ORDERING INFORMATION

Type No.	Marking	Package Code
S8550	2TY	SOT-23

## MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-500	mA
P <sub>C</sub>	Collector Dissipation	300	mW
$T_{j},T_{stg}$	Junction and Storage Temperature	-55~150	$^{\circ}$

# Diode Semiconductor Korea

# Silicon Epitaxial Planar Transistor

S8550

## ELECTRICAL CHARACTERISTICS @ Ta=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μΑ,I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA,I <sub>B</sub> =0	-25		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA,I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-40V,I <sub>E</sub> =0		-0.1	μΑ
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-20V,I <sub>B</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-3V,I <sub>C</sub> =0		-0.1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-1V,I <sub>C</sub> =-50mA	120	350	
		V <sub>CE</sub> =-1V,I <sub>C</sub> =-500mA	50		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> = -50mA		-0.6	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> = -50mA		-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> = -20mA f=30MHz	150		MHz

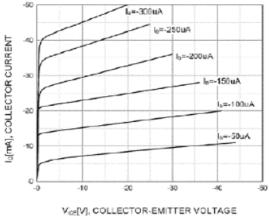
## CLASSIFICATION OF $h_{\text{FE}(1)}$

Rank	L	Н
Range	120-200	200-350

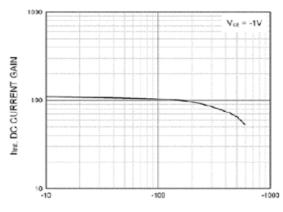
# Silicon Epitaxial Planar Transistor

S8550

## TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

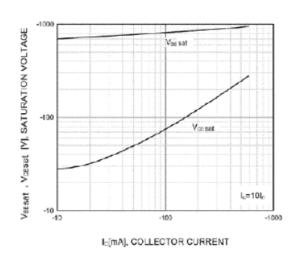


2-3

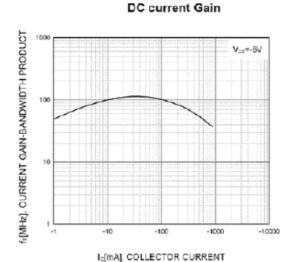


lo[mA], COLLECTOR CURRENT





Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage



**Current Gain Bandwidth Product** 

# Diode Semiconductor Korea

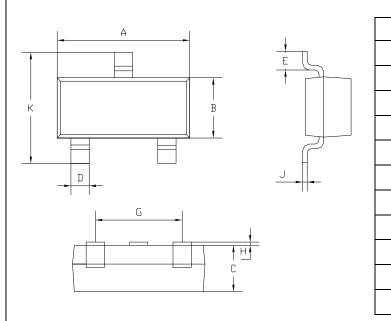
# Silicon Epitaxial Planar Transistor

S8550

## PACKAGE OUTLINE

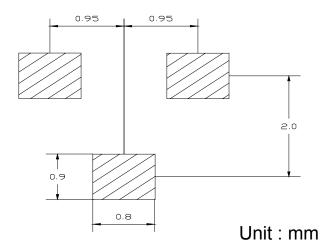
Plastic surface mounted package

SOT-23



SOT-23		
Dim	Min	Max
Α	2.85	2.95
В	1.25	1.35
С	1.0Typical	
D	0.37	0.43
Е	0.35	0.48
G	1.85	1.95
Н	0.02	0.1
J	0.1Typical	
K	2.35	2.45
All Dimensions in mm		

### **SOLDERING FOOTPRINT**



## PACKAGE INFORMATION

Device	Package	Shipping
S8550	SOT-23	3000/Tape&Reel